

BYV25FX-600 Enhanced ultrafast power diode Rev. 02 – 7 March 2011

Product data sheet

Product profile 1.

1.1 General description

Enhanced ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Isolated package
- Low on-state losses

1.3 Applications

- Dual Mode (DCM and CCM) PFC
- Low thermal resistance
- Soft recovery characteristic
- Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Table 1.	Quick reference da	ata				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; T _h ≤ 97 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	5	A
Static cha	racteristics					
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; see <u>Figure 5</u>	-	1.3	1.9	V
		I _F = 5 A; T _j = 150 °C; see <u>Figure 5</u>	-	1.1	1.7	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; see <u>Figure 6</u>	-	17.5	35	ns



2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode	mb	K — Ң A 001aaa020
mb	n.c.	mounting base; isolated		

SOD113 (TO-220F)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BYV25FX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

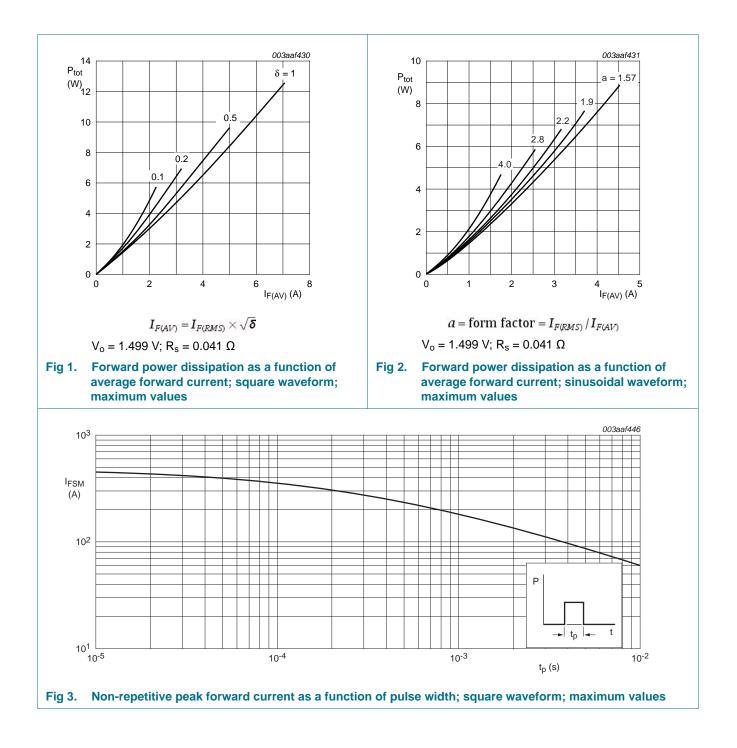
4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; T _h ≤ 97 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	5	A
I _{FRM}	repetitive peak forward current	square-wave pulse; $\delta = 0.5$; $t_p = 25 \ \mu s$; $T_h \le 97 \ ^\circ C$	-	10	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; T _{j(init)} = 25 °C; see <u>Figure 3</u>	-	60	A
		t _p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C; see <u>Figure 3</u>	-	66	A
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

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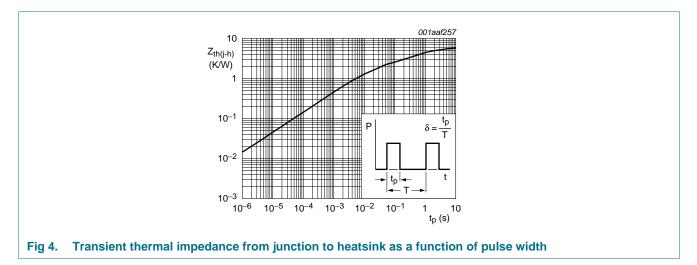
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5. Thermal characteristics

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Table 5.	I hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; see <u>Figure 4</u>	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



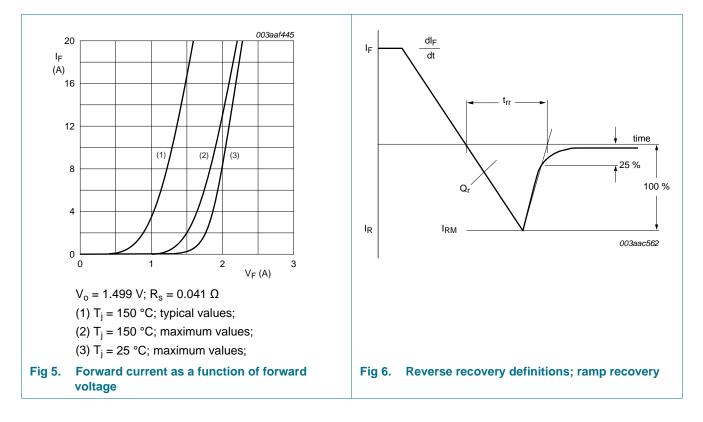
6. Isolation characteristics

Table 6.	Isolation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

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7. Characteristics

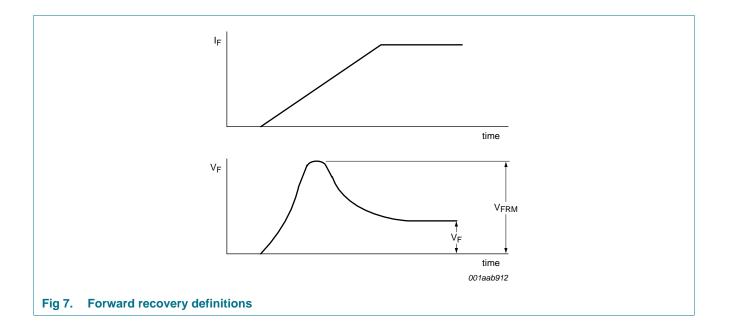
Table 7.	Characteristics						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static cha	Static characteristics						
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{\text{Figure 5}}$	-	1.3	1.9	V	
		I _F = 5 A; T _j = 150 °C; see <u>Figure 5</u>	-	1.1	1.7	V	
I _R	reverse current	$V_R = 600 \text{ V}; \text{ T}_j = 100 \text{ °C}$	-	-	1.5	mA	
		$V_{R} = 600 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	50	μA	
Dynamic	characteristics						
Qr	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 6}{2}$	-	13	-	nC	
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/µs; T _j = 25 °C; see <u>Figure 6</u>	-	17.5	35	ns	
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 6}{2}$	-	1.5	-	А	
V _{FRM}	forward recovery voltage	I _F = 1 A; dI _F /dt = 100 A/μs; T _j = 25 °C; see <u>Figure 7</u>	-	3.2	-	V	



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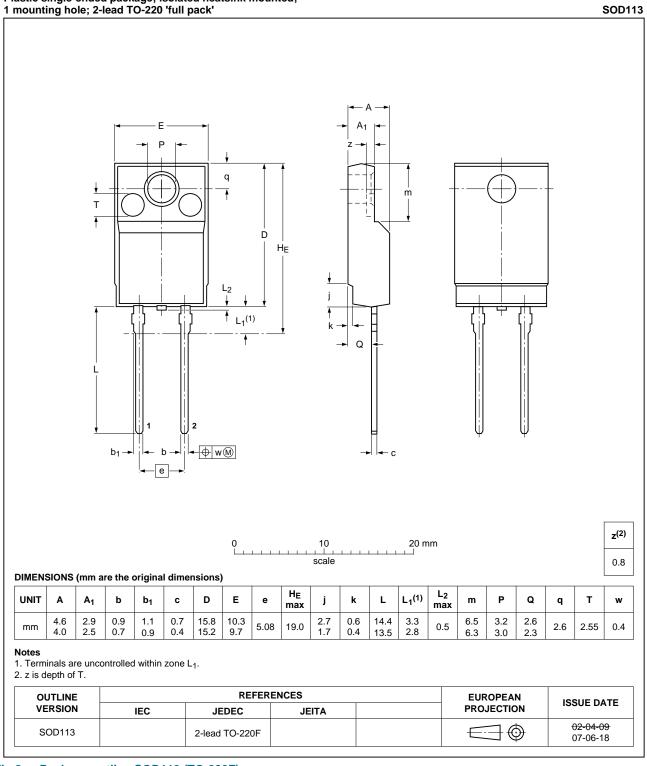
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Package outline 8.



Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

Fig 8. Package outline SOD113 (TO-220F)

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9. Revision history

Table 8.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV25FX-600 v.2	20110307	Product data sheet	-	BYV25FX-600 v.1
Modifications:	 Various chang 	jes to content.		
BYV25FX-600 v.1	20101004	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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